

2N2369A

NPN SILICON TRANSISTOR



TO-18 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N2369A is an epitaxial planar NPN Silicon Transistor designed for ultra high speed saturated switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
 Collector-Emitter Voltage
 Collector-Emitter Voltage
 Emitter-Base Voltage
 Continuous Collector Current
 Peak Collector Current
 Power Dissipation
 Power Dissipation ($T_C=25^\circ\text{C}$)
 Operating and Storage Junction Temperature
 Thermal Resistance
 Thermal Resistance

SYMBOL

V_{CB0} 40
 V_{CES} 40
 V_{CEO} 15
 V_{EBO} 4.5
 I_C 200
 I_{CM} 500
 P_D 360
 P_D 1.2
 T_J, T_{stg} -65 to +200
 θ_{JA} 486
 θ_{JC} 146

UNITS

V
 V
 V
 V
 mA
 mA
 mW
 W
 $^\circ\text{C}$
 $^\circ\text{C/W}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=20\text{V}$		400	nA
I_{CBO}	$V_{CB}=20\text{V}, T_A=150^\circ\text{C}$		30	μA
BV_{CBO}	$I_C=10\mu\text{A}$	40		V
BV_{CES}	$I_C=10\mu\text{A}$	40		V
BV_{CEO}	$I_C=10\text{mA}$	15		V
BV_{EBO}	$I_E=10\mu\text{A}$	4.5		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		200	mV
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}, T_A=125^\circ\text{C}$		300	mV
$V_{CE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}$		250	mV
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		500	mV
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	700	850	mV
$V_{BE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}$		1.15	V
$V_{BE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		1.6	V
h_{FE}	$V_{CE}=0.35\text{V}, I_C=10\text{mA}$	40	120	
h_{FE}	$V_{CE}=0.35\text{V}, I_C=10\text{mA}, T_A=-55^\circ\text{C}$	20		
h_{FE}	$V_{CE}=0.4\text{V}, I_C=30\text{mA}$	30		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	20		

R0 (10-March 2011)

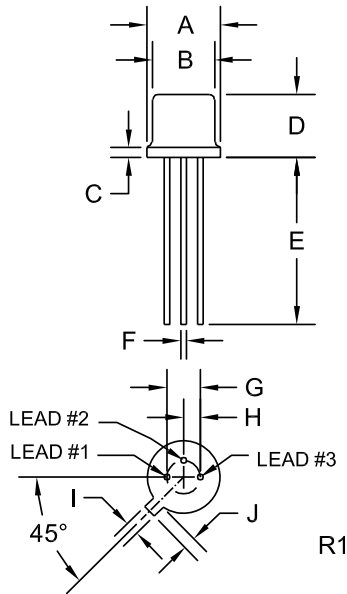
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	500		MHz
C_{ob}	$V_{CB}=5.0\text{V}$, $I_E=0$, $f=140\text{kHz}$		4.0	pF
t_{on}	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=3.0\text{mA}$, $I_{B2}=1.5\text{mA}$		12	ns
t_{off}	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=3.0\text{mA}$, $I_{B2}=1.5\text{mA}$		18	ns
t_s	$V_{CC}=10\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=10\text{mA}$		13	ns

TO-18 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R0 (10-March 2011)